

Cont. of Application Number: 09/739,905
Filing Date: June 24, 2003
Attorney Docket Number: 04329.2470-01

containing oxygen and carbon monoxide, a carbon monoxide gas, and a carbon dioxide gas, is used as the gas containing oxygen atoms and carbon atoms.

39. The semiconductor device manufacturing method according to claim 35, wherein said ashing and removing the photoresist includes setting the substrate temperature to not higher than 150°C.

40. The semiconductor device manufacturing method according to claim 35, wherein said ashing and removing the photoresist includes setting the reaction pressure to not higher than 400 m.Torr.

REMARKS

This application is a continuation, under 37 C.F.R. § 1.53(b), of U.S. Patent Application No. 09/739,905, presently allowed. In this Preliminary Amendment, Applicants have amended the Specification and Abstract, cancelled claims 1 – 20 without prejudice or disclaimer of their subject matter, and added new claims 21 – 40 to protect additional aspects of the present invention. In accordance with the requirements of 37 C.F.R. § 1.121(c)(1), Applicants provide a marked-up version of the amended specification in an attached Appendix designated "Version of Specification with Markings to Show Changes Made."

Applicants respectfully request the Examiner promptly consider and allow this application.

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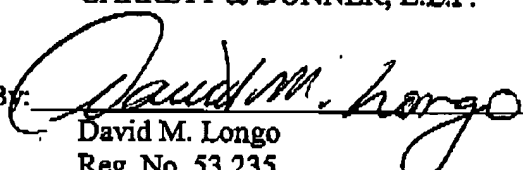
If there is any fee due in connection with the filing of this Preliminary Amendment,
please charge the fee to our Deposit Account No. 06-0916.

Respectfully submitted,

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Dated: June 24, 2003

By:


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